

Parameter	Value
Sintered Density	$> 3.10 \text{ g cm}^{-3}$
Young's Modulus	400 GPa
Poisson Ratio	0.16
Vickers Hardness HV500	25.7 GPa
Fracture Toughness (indentation with 5 N load)	$3.9 \text{ MPa m}^{1/2}$
Thermal Conductivity	$120 \text{ W mK}^{-1}$
Strength (4-point-flexural test)*	400 MPa
Coefficient of Linear Thermal Expansion at RT	$3.3 \times 10^{-6} \text{ K}^{-1}$
Porosity	1 %–2 %
Specific Electrical Resistance, depending on impurity level of SiC	$10^2\text{--}10^4 \text{ }\Omega\text{cm}$
Microstructure, depending on shape forming and sintering conditions	20–50 $\mu\text{m}$
Maximal Pore Size	
Maximal Crystal Size	35 $\mu\text{m}$